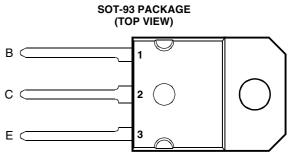
# BD250, BD250A, BD250B, BD250C PNP SILICON POWER TRANSISTORS

# BOURNS®

- Designed for Complementary Use with the BD249 Series
- 125 W at 25°C Case Temperature
- 25 A Continuous Collector Current
- 40 A Peak Collector Current
- Customer-Specified Selections Available



Pin 2 is in electrical contact with the mounting base.

#### absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT		
	BD250		-55		
Callester emitter veltere (D. 100.0)	BD250A		-70	v	
Collector-emitter voltage ( $R_{BE} = 100 \Omega$ )	BD250B	VCER	-90	v	
	BD250C		-115		
	BD250		-45		
Collector-emitter voltage ( $I_c = -30$ mA)	BD250A	V	-60	v	
	BD250B	V <sub>CEO</sub>	-80	v	
	BD250C		-100		
Emitter-base voltage		V <sub>EBO</sub>	-5	V	
Continuous collector current		Ι <sub>C</sub>	-25	A	
Peak collector current (see Note 1)		I <sub>CM</sub>	-40	A	
Continuous base current		I <sub>B</sub>	-5	А	
Continuous device dissipation at (or below) 25°C case temperature (see Note 2	)	P <sub>tot</sub>	125	W	
Continuous device dissipation at (or below) 25°C free air temperature (see Note	3)	P <sub>tot</sub>	3	W	
Unclamped inductive load energy (see Note 4)		1/2LI <sub>C</sub> 2	90	mJ	
Operating junction temperature range		Тj	-65 to +150	°C	
Storage temperature range		T <sub>stg</sub>	-65 to +150	°C	
Lead temperature 3.2 mm from case for 10 seconds		Τ <sub>L</sub>	250	°C	

NOTES: 1. This value applies for  $t_p \leq 0.3$  ms, duty cycle  $\leq 10\%.$ 

2. Derate linearly to 150°C case temperature at the rate of 1 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 24 mW/°C.

4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH,  $I_{B(on)}$  = -0.4 A,  $R_{BE}$  = 100  $\Omega$ ,  $V_{BE(off)}$  = 0,  $R_S$  = 0.1  $\Omega$ ,  $V_{CC}$  = -20 V.

### PRODUCT INFORMATION

# BD250, BD250A, BD250B, BD250C PNP SILICON POWER TRANSISTORS



#### electrical characteristics at 25°C case temperature

PARAMETER			TEST CONDITION	IS	ТҮР	MAX	UNIT	
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> = -30 mA (see Note 5)	I <sub>B</sub> = 0	BD250 BD250A BD250B BD250C	-45 -60 -80 -100			v
I <sub>CES</sub>	Collector-emitter cut-off current	$V_{CE} = -55 V \\ V_{CE} = -70 V \\ V_{CE} = -90 V \\ V_{CE} = -115 V$	$V_{BE} = 0$	BD250 BD250A BD250B BD250C			-0.7 -0.7 -0.7 -0.7	mA
I <sub>CEO</sub>	Collector cut-off current	$V_{CE} = -30 V$ $V_{CE} = -60 V$	I <sub>B</sub> = 0 I <sub>B</sub> = 0	BD250/250A BD250B/250C			-1 -1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> = -5 V	I <sub>C</sub> = 0				-1	mA
h <sub>FE</sub>	Forward current transfer ratio	$V_{CE} = -4 V$ $V_{CE} = -4 V$ $V_{CE} = -4 V$	I <sub>C</sub> = -15 A	(see Notes 5 and 6)	25 10 5			
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage		I <sub>C</sub> = -25 A	(see Notes 5 and 6)			-1.8 -4	V
V <sub>BE</sub>	Base-emitter voltage	$V_{CE} = -4 V$ $V_{CE} = -4 V$	I <sub>C</sub> =  -15 A I <sub>C</sub> =  -25 A	(see Notes 5 and 6)			-2 -4	V
h <sub>fe</sub>	Small signal forward current transfer ratio	V <sub>CE</sub> = -10 V	I <sub>C</sub> = - 1A	f = 1 kHz	25			
h <sub>fe</sub>	Small signal forward current transfer ratio	V <sub>CE</sub> = -10 V	I <sub>C</sub> = -1 A	f = 1 MH2	3			

NOTES: 5. These parameters must be measured using pulse techniques,  $t_p = 300 \ \mu s$ , duty cycle  $\leq 2\%$ .

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

#### thermal characteristics

PARAMETER	MIN	ТҮР	MAX	UNIT
R <sub>0JC</sub> Junction to case thermal resistance			1	°C/W
R <sub>0JA</sub> Junction to free air thermal resistance			42	°C/W

#### resistive-load-switching characteristics at 25°C case temperature

	PARAMETER	TEST CONDITIONS <sup>†</sup>			MIN	ТҮР	MAX	UNIT
t <sub>on</sub>	Turn-on time	I <sub>C</sub> = -5 A	I <sub>B(on)</sub> = -0.5 A	$I_{B(off)} = 0.5 A$		0.2		μs
t <sub>off</sub>	Turn-off time	$V_{BE(off)} = 5 V$	$R_L = 5 \Omega$	$t_p$ = 20 µs, dc $\leq$ 2%		0.4		μs

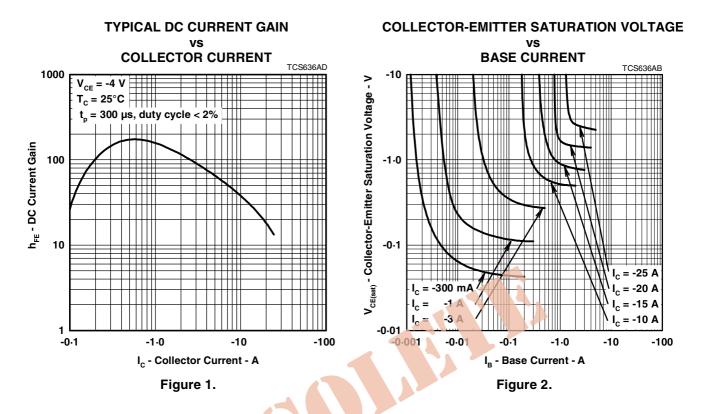
<sup>†</sup> Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

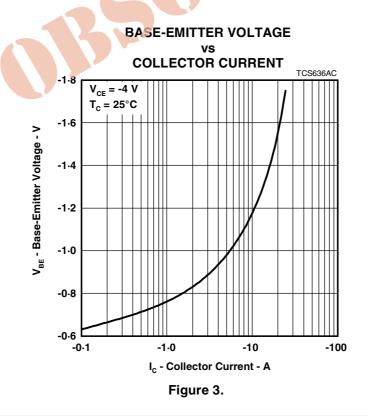




## BD250, BD250A, BD250B, BD250C PNP SILICON POWER TRANSISTORS

### **TYPICAL CHARACTERISTICS**

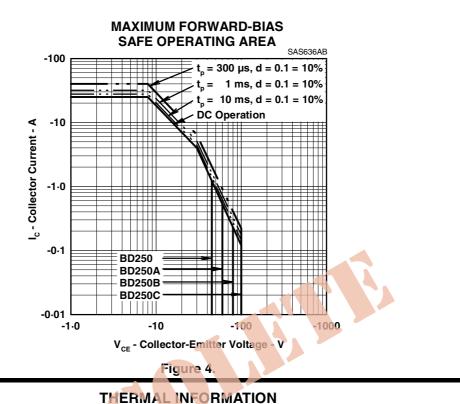




### PRODUCT INFORMATION

JUNE 1973 - REVISED SEPTEMBER 2002 Specifications are subject to change without notice.

#### MAXIMUM SAFE OPERATING REGIONS



MAXIMUM POWER DISSIPATION VS **CASE TEMPERATURE** TIS635AA 140 P<sub>rot</sub> - Maximum Power Dissipation - W 0 09 08 00 07 20 0 0 25 50 75 100 125 150 T<sub>c</sub> - Case Temperature - °C

